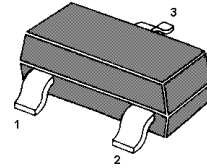


MMBTSC3324

NPN Silicon Epitaxial Planar Transistor

for audio frequency low noise amplifier applications.

The transistor is subdivided into two groups G and L, according to its DC current gain.



1. Base 2. Emitter 3. Collector

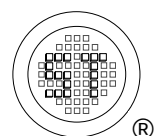
TO-236 Plastic Package

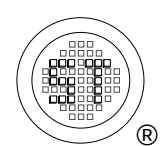
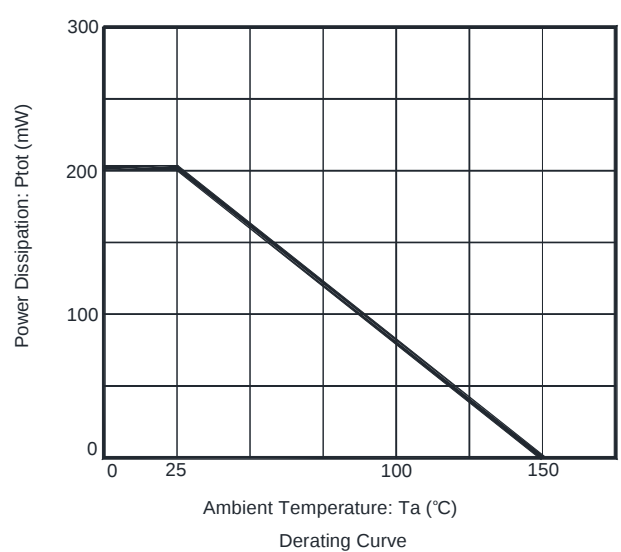
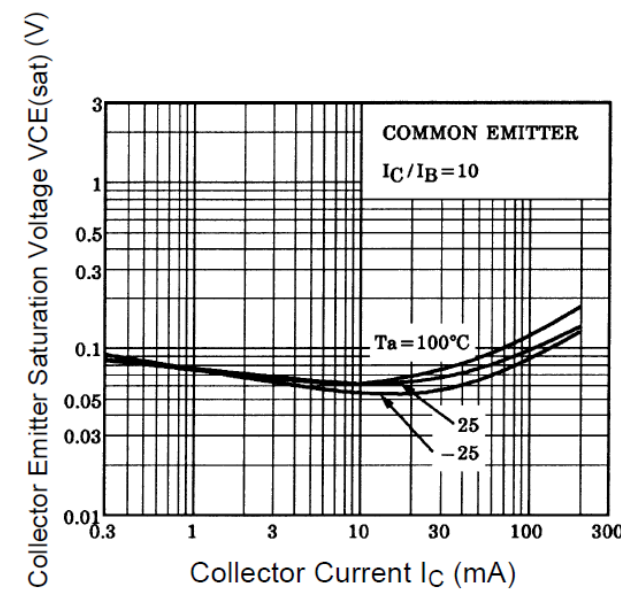
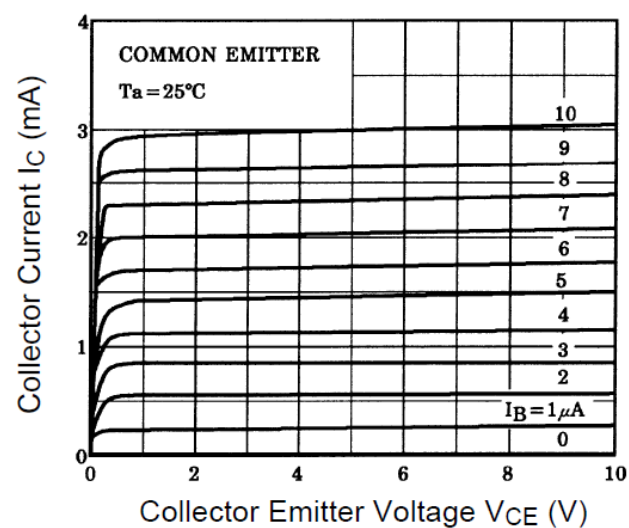
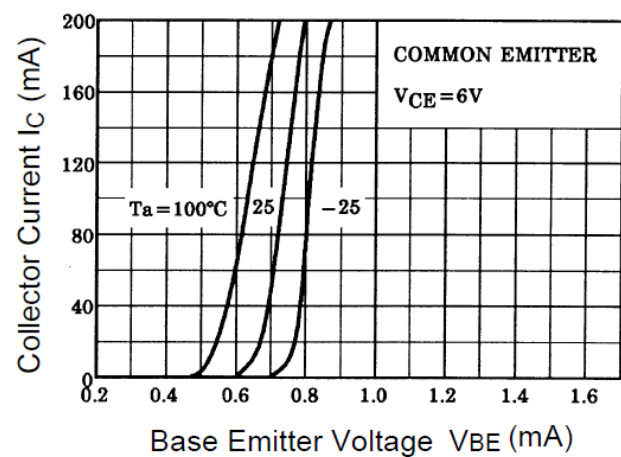
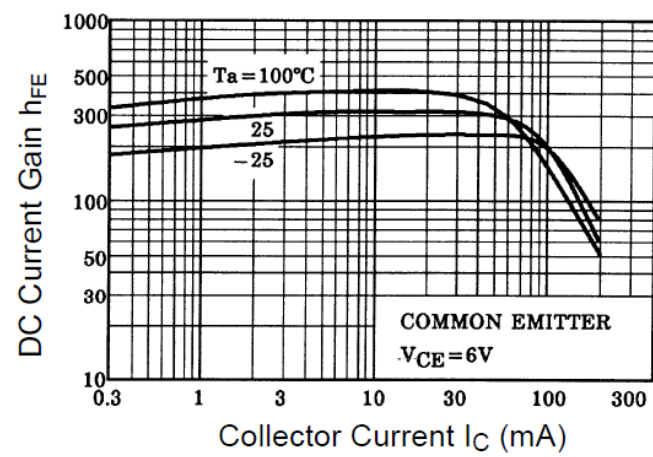
Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	120	V
Collector Emitter Voltage	V_{CEO}	120	V
Emitter Base Voltage	V_{EBO}	5	V
Collector Current	I_C	100	mA
Base Current	I_B	20	mA
Collector Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 125	$^\circ\text{C}$

Characteristics at $T_a=25^\circ\text{C}$

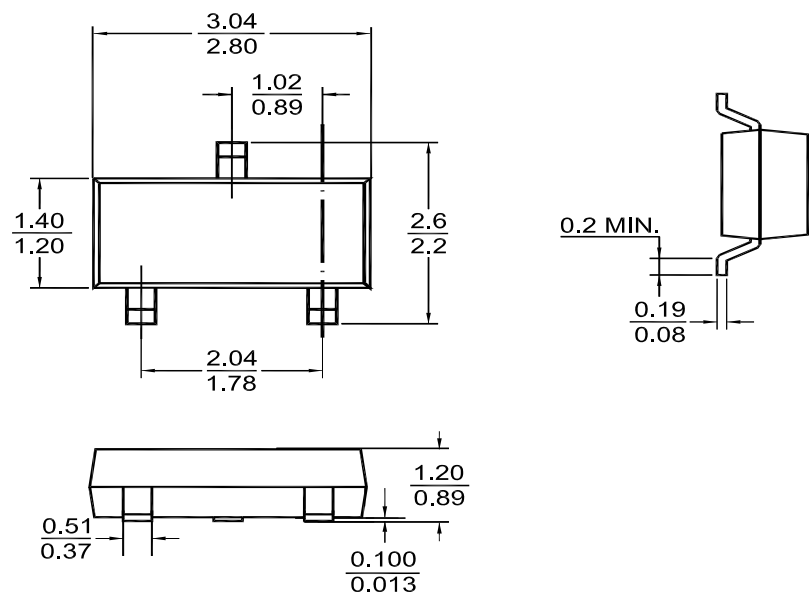
Parameter	Symbol	Min.	Typ.	Max.	Unit	
DC Current Gain at V _{CE} = 6 V, I _C = 2 mA	G	h _{FE}	200	-	400	-
	L	h _{FE}	350	-	700	-
Collector Base Cut-off Current at V _{CB} = 120 V	I _{CBO}	-	-	0.1	μA	
Emitter Base Cut-off Current at V _{EB} = 5 V	I _{EBO}	-	-	0.1	μA	
Collector Emitter Saturation Voltage at I _C = 10 mA, I _B = 1 mA	V _{CE(sat)}	-	-	0.3	V	
Transition Frequency at V _{CE} = 6 V, I _C = 1 mA	f _T	-	100	-	MHz	
Collector Output Capacitance at V _{CB} = 10 V, f = 1 MHz	C _{ob}	-	4	-	pF	



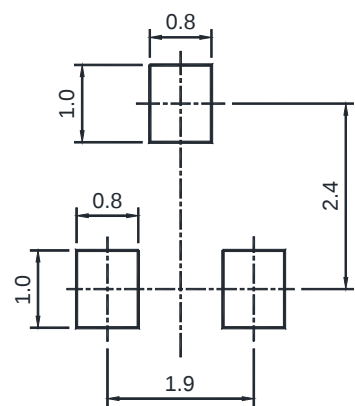


Package Outline (Dimensions in mm)

TO-236



Recommended Soldering Footprint



Packing information

Package	Tape Width (mm)	Pitch		Reel Size		Per Reel Packing Quantity
		mm	inch	mm	inch	
TO-236	8	4 ± 0.1	0.157 ± 0.004	178	7	3,000

